



### Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

50 / -60V

Current

0.36A / -0.2A

### **Features**

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

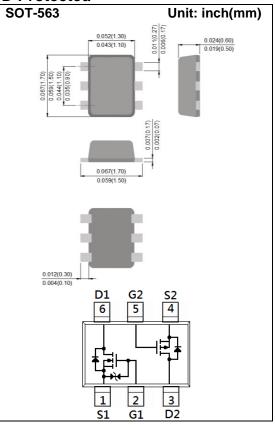
#### **Mechanical Data**

• Case: SOT-563 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0026 grams

Marking: X63



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	50	-60	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 20	<u>+</u> 20	V
Continuous Drain Current		I <sub>D</sub>	360	-200	mA
Pulsed Drain Current <sup>(Note 4)</sup>		I <sub>DM</sub>	1200	-900	mA
Power Dissipation	T <sub>a</sub> =25°C	_	300		mW
	Derate above 25°C	l P <sub>D</sub>	2	mW/°C	
Operating Junction and Storage Tem	T <sub>J</sub> ,T <sub>STG</sub>	-55~150		°C	
Typical Thermal Resistance					
- Junction to Ambient <sup>(Note 3)</sup>		Reja	417		°C/W





### N-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = 250uA	50	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = 250uA	0.5	0.9	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 500mA	-	1.26	1.5	Ω
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA	-	1.34	2.5	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 50V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 10	uA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V	-	0.95	-	nC
Gate-Source Charge	$Q_gs$		-	0.34	-	
Gate-Drain Charge	$Q_gd$		-	0.32	-	
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	36	-	pF
Output Capacitance	Coss		-	11	-	
Reverse Transfer Capacitance	Crss		-	6.6	-	
Turn-On Delay Time	td <sub>(on)</sub>	. \/ O5\/   500 A	-	2.3	-	
Turn-On Rise Time	tr	$\begin{array}{c} V_{DD}{=}25V,\ I_{D}{=}500mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega^{(Note\ 1,2)} \end{array}$	-	20	-	ns -
Turn-Off Delay Time	td <sub>(off)</sub>		-	7	-	
Turn-Off Fall Time	tf		-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I.			-	360	mA
Diode Forward Current	Is		-			
Diode Forward Voltage	$V_{\text{SD}}$	Is= 500mA, V <sub>GS</sub> =0V	-	0.9	1.5	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





## P-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance		V <sub>GS</sub> =-10V,I <sub>D</sub> =-500mA	-	2.6	6	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-200mA	ı	2.9	7	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-48V,V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic <sup>(Note 5)</sup>						
Total Gate Charge	Qg	V <sub>DS</sub> =-25V, I <sub>D</sub> =-100mA, V <sub>GS</sub> =-4.5V	-	1.1	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.3	-	
Gate-Drain Charge	$Q_{gd}$		-	0.2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	51	-	pF
Output Capacitance	Coss		-	15	-	
Reverse Transfer Capacitance	Crss		-	2.2	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	4.8	-	ns
Turn-On Rise Time	tr	V <sub>DD</sub> =-25V, I <sub>D</sub> =-100mA, V <sub>GS</sub> =-10V,	-	19	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	52	-	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note 1,2)}$	-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	,		-	-	-200	mA
Diode Forward Current	Is					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-500mA, V <sub>GS</sub> =0V	-	-0.9	-1.5	V





#### **N-Channel TYPICAL CHARACTERISTIC CURVES**

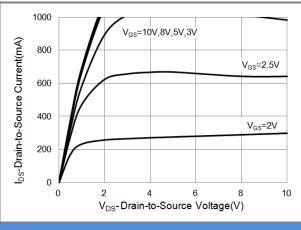


Fig.1 On-Region Characteristics

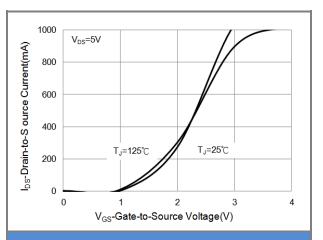


Fig.2 Transfer Characteristics

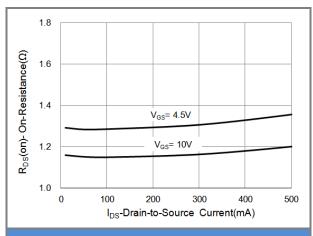


Fig.3 On-Resistance vs. Drain Current

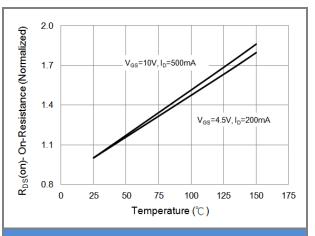


Fig.4 On-Resistance vs. Junction temperature

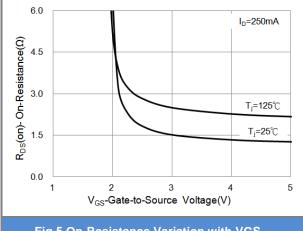
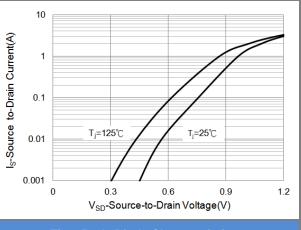


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 





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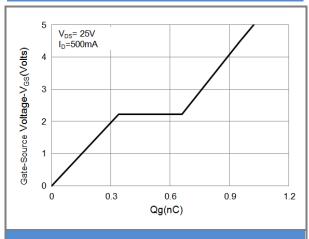


Fig.7 Gate-Charge Characteristics

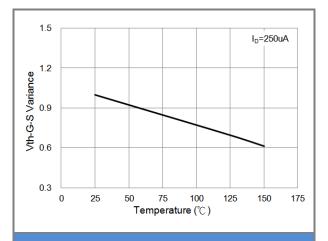


Fig.8 Threshold Voltage Variation with Temperature.

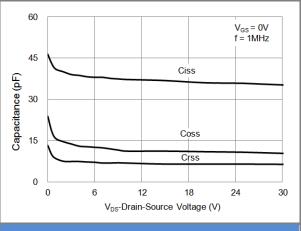


Fig.9 Capacitance vs. Drain-Source Voltage.





#### P-Channel TYPICAL CHARACTERISTIC CURVES

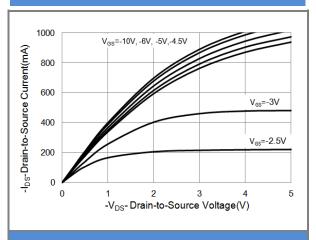
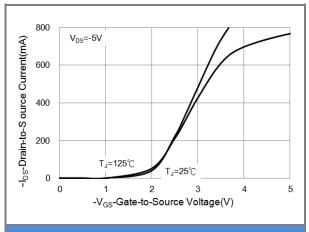


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

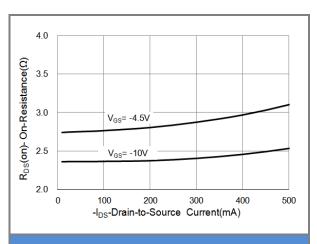


Fig.3 On-Resistance vs. Drain Current

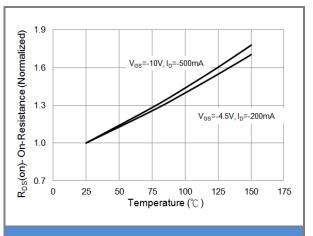


Fig.4 On-Resistance vs. Junction temperature

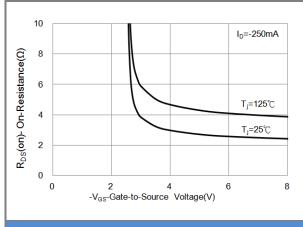
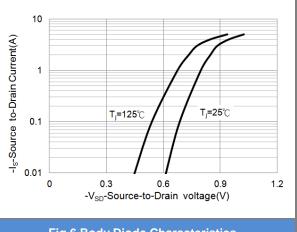


Fig.5 On-Resistance Variation with VGS.

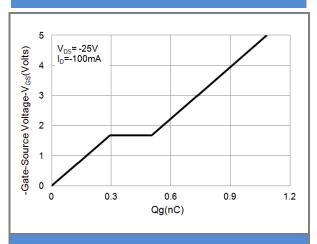


**Fig.6 Body Diode Characteristics** 





### P-Channel TYPICAL CHARACTERISTIC CURVES



**Fig.7 Gate-Charge Characteristics** 

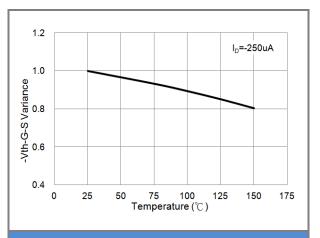


Fig.8 Threshold Voltage Variation with Temperature.

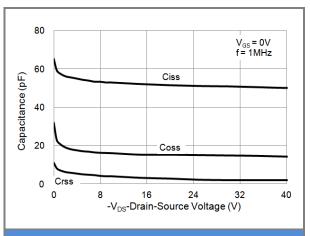


Fig.9 Threshold Voltage Variation with Temperature.

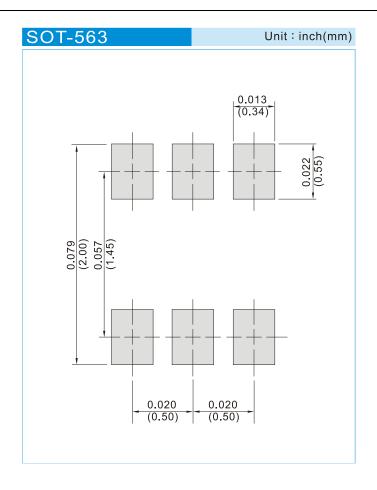




### PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJX8603_R1_00001	SOT-563	4K pcs / 7" reel	X63	Halogen free RoHS compliant
PJX8603_R2_00001	SOT-563	10K pcs / 13" reel	X63	Halogen free RoHS compliant
PJX8603_R1_00002	SOT-563	8K pcs / 7" reel	X63	Halogen free RoHS compliant
PJX8603_R2_00002	SOT-563	20K pcs / 13" reel	X63	Halogen free RoHS compliant

### **MOUNTING PAD LAYOUT**







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